

Am29705A/707

16-Word by 4-Bit 2-Port RAM

DISTINCTIVE CHARACTERISTICS

- 16-word by 4-bit, 2-port RAM
- Two output ports, each with separate output control
- Separate four-bit latches on each output port (Am29707 has separate output control)
- Data output is noninverting with respect to data input
- Chip select and write enable inputs for ease in cascading
- Am29707 offers 20% improved cycle time over Am29705A when used with Am29203 in three address architecture
- Am29705A is a pin-for-pin replacement for the Am29705 but is significantly faster on critical paths

GENERAL DESCRIPTION

The Am29705A is a 16-word by 4-bit, two-port RAM. This RAM features two separate output ports such that any two 4-bit words can be read from these outputs simultaneously. Each output port has a four-bit Latch but a common Latch Enable (LE) input is used to control all eight latches. The device has two Write Enable (WE) inputs and is designed such that the Write Enable 1 (WE₁) and Latch Enable (LE) inputs can be wired together to make the operation of the RAM appear edge triggered.

The device has a fully decoded four-bit A-address field to address any of the 16 memory words for the A-output port. Likewise, a four-bit B-address input is used to simultaneously select any of the 16 words for presentation at the B-output port. New incoming data is written into the four-bit RAM word selected by the B-address. The D inputs are used to load new data into the device.

The Am29705A features three-state outputs and several devices can be cascaded to increase the total number of memory words in the system. The A-output port is in the high-impedance state when the OE-A input is HIGH.

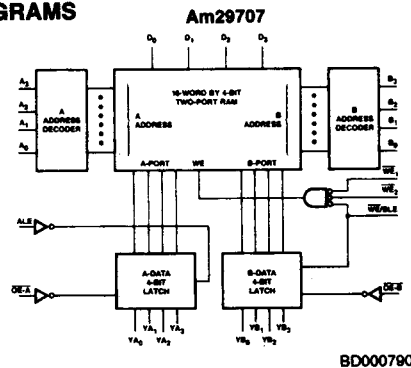
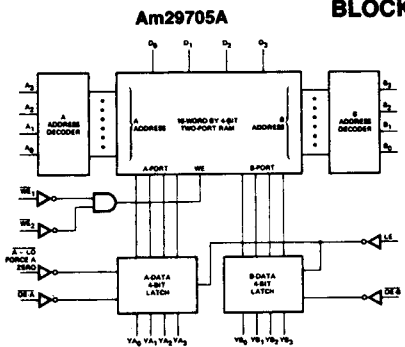
Likewise, the B-output port is in the high-impedance state when the OE-B input is HIGH. Four devices can be paralleled using only one Am25LS139 decoder for output control.

The Write Enable inputs control the writing of new data into the RAM. When both Write Enable inputs are LOW, new data is written into the word selected by the B-address field. When either Write Enable input is HIGH, no data is written into the RAM.

The Am29707 is an identical circuit to the Am29705A, except each output port has a separate Latch Enable (LE) input. An extra write enable input (WE₂) may be connected directly to the IEN of the Am29203 for improved cycle times over the Am29705A. The WE/BLE input can then be connected directly to system clock.

The Am29705A is a plug-in replacement for the Am29705, but is significantly faster. The Am29705A and Am29707 feature AMD's advanced ion-implanted micro-oxide (IMOX™) processing.

BLOCK DIAGRAMS



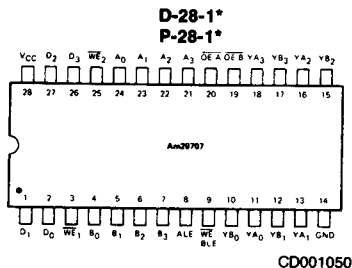
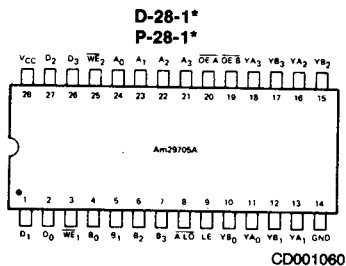
RELATED PRODUCTS

Am29751A Bipolar PROM
 Am2921 One-of-Eight Decoder
 Am25LS138 One-of-Four Decoder
 Am25LS139 Dual One-of-Four Decoder
 Am25LS157 Quad 2-by-1 MUX
 Am29203 Four Bit Bipolar Microprocessor Slice
 Am2902A Carry Look Ahead Generator

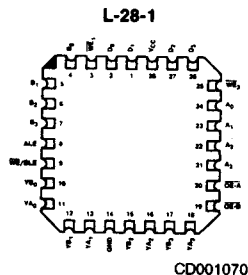
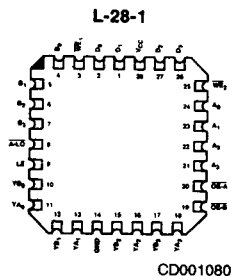
Am2904
 Am2910A
 Am2914
 Am2940
 Am2950-54
 Am29118

Status and Shift Control Unit
 Microprogram Controller
 Vectored Priority Interrupt Controller
 DMA Address Generator
 8 Bit Bidirectional I/O Port
 8 Bit Bidirectional I/O Port with ACC

CONNECTION DIAGRAMS - TOP VIEWS

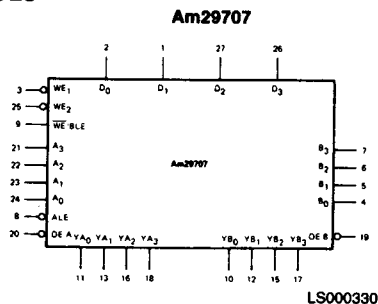
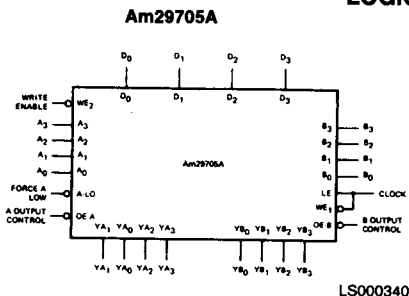


*Devices are also offered in a 28 pin flatpak.
Connections are the same as DIPs.

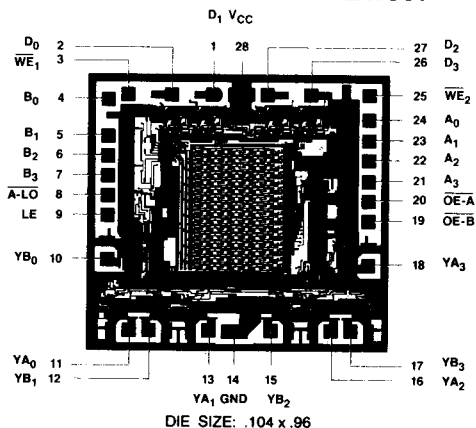


Note: Pin 1 is marked for orientation

LOGIC SYMBOLS



METALLIZATION AND PAD LAYOUT



ORDERING INFORMATION

Am29707 A D C B

Part Number

Speed
See Product Select Guide

Burn-In Option
B = 96 hour burn-in

Temperature Range
C = 0 to +70°C
M = -55 to +125°C

Package
D = 28 pin ceramic SLIMDIP
F = 28 pin Flat Pak
L = 28 pin Chip Pak
P = 28 pin Molded Dip
X = 28 Dice

Valid Combinations	
Am29707	DC, DCB, DMB, FMB, LC, LMB, PC, XC, XM
Am29707	DC, DCB, DMB, FMB, LC, LMB, PC, XC, XM

PIN DESCRIPTION

D₀ - D₃	Data Inputs New data is written into the RAM through these inputs.
A₀ - A₃	The A-Address Inputs The four-bit field presented at the A inputs selects one of the 16 memory words for presentation to the A-Data Latch.
B₀ - B₃	The B-Address Inputs The four bit field presented at the B inputs selects one of the 16 memory words for presentation to the B-Data Latch. The B address field also selects the word into which new data is written.
YA₀ - YA₃	The Four A-Data Latch Outputs
YB₀ - YB₃	The Four B-Data Latch Outputs
WE₁, WE₂	Write Enables When both Write Enables are LOW, new data is written into the word selected by the B-address field. If either Write Enable input is HIGH, no new data can be written into the memory.
$\overline{OE-A}$	A-Port Output Enable When $\overline{OE-A}$ is LOW, data in the A-Data Latch is present at the YA _i outputs. If $\overline{OE-A}$ is HIGH the YB _i outputs are in the high-impedance (off) state.
$\overline{OE-B}$	B-Port Output Enable When $\overline{OE-B}$ is LOW, data in the B-Data Latch is present at the YB _i outputs. When $\overline{OE-B}$ is HIGH the YB _i outputs are in the high-impedance (off) state.

LE**Latch Enable**

The LE input controls the latches for both the RAM A-output port and RAM B-output port. When the LE input is HIGH, the latches are open (transparent) and data from the RAM, as selected by the A and B address fields, is present at the outputs. When LE is LOW, the latches are closed and they retain the last data read from the RAM independent of the current A and B address field inputs. (Am29705A only.)

 $\overline{A-L0}$ **Force A Zero**

This input is used to force the outputs of the A-port latches LOW independent of the Latch Enable input or A-address field select inputs. Thus, the A-output bus can be forced LOW using this control signal. When the $\overline{A-L0}$ input is HIGH, the A latches operate in their normal fashion. Once the A latches are forced LOW, they remain LOW independent of the $\overline{A-L0}$ input if the latches are closed. (Am29705A only.)

ALE**A-Output Port Latch Enable**

When ALE is HIGH, the A latch is open (transparent) and data from the RAM, as selected by the A address field, is present at the A output. When ALE is LOW, the A latch is closed and retains the last data read from the RAM independent of the current A address field input. (Am29707 only.)

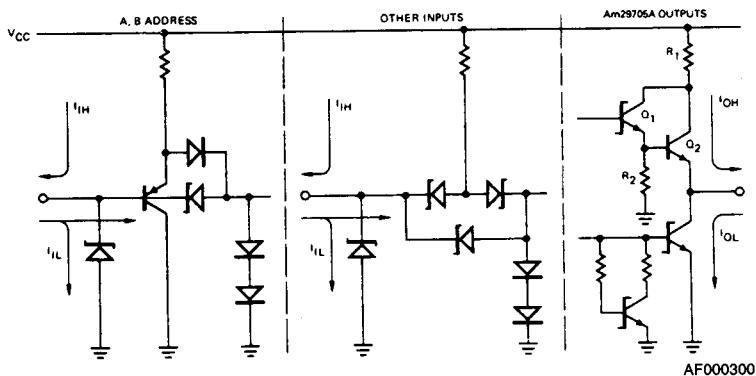
WE/BLE**Write Enable/B-Output Port Latch Enable**

When WE/BLE is LOW together with WE₁ and WE₂, new data is written into the word selected by the B address field. When WE/BLE or any Write Enable input is HIGH, no data is written into the RAM.

WE/BLE also controls the B output port. When WE/BLE is HIGH, the B latch is open (transparent), and when this input is LOW, the B latch is closed (Am29707 only).

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INPUT/OUTPUT CURRENT INTERFACE CONDITIONS



Note: Actual current flow direction shown.

FUNCTION TABLES

Am29705A

WRITE CONTROL

WE ₁	WE ₂	Function	RAM Outputs at Latch Inputs	
			A-Port	B-Port
L	L	Write D into B	A data (A ≠ B)	Input Data
L	L	Write D into B	(A = B) Input Data	Input Data
X	H	No Write	A Data	B Data
H	X	No Write	A Data	B Data

H = HIGH L = LOW X = Don't Care

YA READ

Inputs			YA Output	Function
OE-A	A-LO	LE		
H	X	X	Z	High Impedance
L	L	X	L	Force YA LOW
L	H	H	A-Port RAM Data	Latches Transparent
L	H	L	NC	Latches Retain Data

H = HIGH X = Don't Care NC = No Change
L = LOW Z = High Impedance

YB READ

Inputs		YB Output	Function
OE-B	LE		
H	X	Z	High Impedance
L	H	B-Port RAM Data	Latches Transparent
L	L	NC	Latches Retain Data

H = HIGH X = Don't Care NC = No change
L = LOW Z = High Impedance

Am29707

WRITE CONTROL

WE ₁	WE ₂	WE/BLE	Function	RAM Outputs at Latch Inputs	
				A-Port	B-Port
L	L	L	Write D into B	A Data (A = B)	Input Data
X	X	H	No Write	A Data	B Data
X	H	X	No Write	A Data	B Data
H	X	X	No Write	A Data	B Data

H = HIGH L = LOW X = Don't Care

YA READ

Inputs		YA Output	Function
OE-A	ALE		
H	X	Z	High Impedance
L	H	A-Port RAM Data	Latches Transparent
L	L	NC	Latches Retain Data

H = HIGH D = Don't Care NC = No Change
L = LOW Z = High Impedance

YB READ

Inputs		YB Output	Function
OE-B	WE/BLE		
H	X	Z	High Impedance
L	H	B-Port RAM Data	Latches Transparent
L	L	NC	Latches Retain Data

H = HIGH D = Don't Care NC = No Change
L = LOW Z = High Impedance

LOADING RULES (In Unit Loads)

Input/Output	Pin No.'s	Input Unit Load	Fan-out Output	
			HIGH	LOW
D ₁	1	1	-	-
D ₀	2	1	-	-
WE ₁	3	1	-	-
B ₀	4	0.55	-	-
B ₁	5	0.55	-	-
B ₂	6	0.55	-	-
B ₃	7	0.55	-	-
A-LO (29705A Only)	8	1	-	-
LE (29705A Only)	9	1	-	-
ALE (29707 Only)	8	1	-	-
WE/BLE (29707 Only)	9	1	-	-
YB ₀	10	-	100/200	33
YA ₀	11	-	100/200	33

Input/Output	Pin No.'s	Input Unit Load	Fan-out Output	
			HIGH	LOW
YB ₁	12	-	100/200	33
YA ₁	13	-	100/200	33
GND	14	-	-	-
YB ₂	15	-	100/200	33
YA ₂	16	-	100/200	33
YB ₃	17	-	100/200	33
YA ₃	18	-	100/200	33
OE-B	19	1	-	-
OE-A	20	1	-	-
A ₃	21	0.55	-	-
A ₂	22	0.55	-	-
A ₁	23	0.55	-	-
A ₀	24	0.55	-	-
WE ₂	25	1	-	-
D ₃	26	1	-	-
D ₂	27	1	-	-
VCC	28	-	-	-

ABSOLUTE MAXIMUM RATINGS

Storage Temperature	-65°C to +150°C
Ambient Temperature with Power Applied	-55°C to +125°C
Supply Voltage to Ground Potential Continuous	-0.5V to +7.0V
DC Voltage Applied to OUPut for HIGH Output State	-0.5V to +V _{CCmax}
DC Input Voltage	-0.5V to +5.5V
DC Output Current, Into Output	30mA
DC Input Current	-30mA to +5.0mA

Stresses above those listed under **ABSOLUTE MAXIMUM RATINGS** may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices	
Temperature	0°C to +70°C
Supply Voltage	+4.75V to +5.25V
Military (M) Devices	
Temperature	-55°C to +125°C
Supply Voltage	+4.5V to +5.5V
Operating ranges define those limits over which the functionality of the device is guaranteed.	

DC CHARACTERISTICS over operating range unless otherwise specified

Symbol	Parameter	Test Conditions (Note 1)	Min	Typ (Note 2)	Max	Units
V _{OH}	Output HIGH Voltage	V _{CC} = MIN. V _{IN} = V _{IH} or V _{IL}	MIL, I _{OH} = -2.0mA 2.4 COM'L, I _{OH} = -4.0mA 2.4			Volts
V _{OL}	Output LOW Voltage	V _{CC} = MIN. V _{IN} = V _{IH} or V _{IL}	I _{OL} = 16mA (MIL) I _{OL} = 20mA (COM)		0.5 0.5	Volts
V _{IH}	Input HIGH Level	Guaranteed input logical HIGH voltage for all inputs	2.0			Volts
V _{IL}	Input LOW Level	Guaranteed input logical LOW voltage for all inputs			0.8	Volts
V _I	Input Clamp Voltage	V _{CC} = MIN., I _{IN} = -18mA			-1.5	Volts
I _{IL}	Input LOW Current	V _{CC} = MAX., V _{IN} = 0.5V	All		-0.36	mA
I _{IH}	Input HIGH Current	V _{CC} = MAX., V _{IN} = 2.7V			20	μA
I _I	Input HIGH Current	V _{CC} = MAX., V _{IN} = 55V			0.1	mA
I _O	Off State (High Impedance) Output Current	V _{CC} = MAX. V _{IN} = V _{IH} or V _{IL}	V _O = 2.4V V _O = 0.5V		20 -20	μA
I _{SC}	Output Short Circuit Current (Note 3)	V _{CC} = MAX.	-30		-85	mA
I _{CC}	Power Supply Current	V _{CC} = MAX. (Worst case I _{CC} is at minimum temperature) (Note 4)	T _A = 0°C to +70°C T _A = 70°C T _C = -55°C to +125°C T _C = 125°C		210 170 210 150	mA

Notes:

- For conditions shown as MIN. or MAX., use the appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical limits are at V_{CC} = 5.0V, 25°C ambient and maximum loading.
- Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.
- All inputs grounded except $\overline{OE-A}$ and $\overline{OE-B}$ = 2.4V.

SWITCHING CHARACTERISTICS over operating range unless otherwise specified

Parameters	From	To	Test Conditions	COM'L	MIL
Access Time	A Address Stable or B Address Stable	YA Stable or YB Stable	LE = HIGH	25	30
Turn-On Time	\overline{OE} -A or \overline{OE} -B LOW	YA or YB Stable		20	20
Turn-Off Time	\overline{OE} -A or \overline{OE} -B HIGH	YA or YB Off	$C_L = 5pF$ Note 1	20	20
Reset Time	\overline{A} -LO LOW	YA LOW		20	20
Latch Enable Time	LE HIGH	YA and YB Stable		20	22
Transparency	\overline{WE}_1 and \overline{WE}_2 LOW	YA or YB	LE = HIGH	30	35
	D	YA or YB	LE = HIGH	30	35

Note 1. Measured from 1.5V at the input to 0.5V change in the output level.

MINIMUM SETUP AND HOLD TIME (in ns)

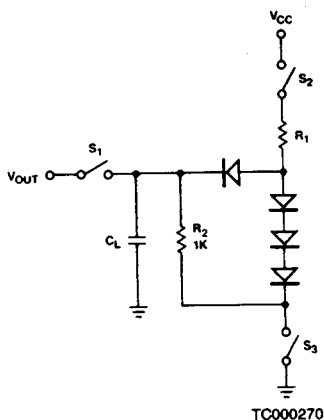
Parameters	From	To	Test Conditions	COM'L	MIL
Data Setup Time	D Stable	Either \overline{WE} HIGH		12	15
Data Hold Time	Either \overline{WE}	D Changing		0	0
Address Setup Time	B Stable	Both \overline{WE} LOW		6	8
Address Hold Time	Either \overline{WE} HIGH	B Changing		0	0
Latch Close Before Write Begins	LE LOW	\overline{WE}_1 LOW	\overline{WE}_2 LOW	0	0
	LE LOW	\overline{WE}_2 LOW	\overline{WE}_1 LOW	0	0
Address Setup Before Latch Closes	A or B Stable	LE LOW		12	15

MINIMUM PULSE WIDTHS

Parameters	Input	Pulse	Test Conditions	COM'L	MIL
Write Pulse Width	\overline{WE}_1	HIGH-LOW-HIGH	\overline{WE}_2 LOW	15	15
	\overline{WE}_2	HIGH-LOW-HIGH	\overline{WE}_1 LOW	15	15
A Latch Reset Pulse	\overline{A} -LO	HIGH-LOW-HIGH		15	15
Latch Data Capture	LE	LOW-HIGH-LOW		15	18

Note: The Am29705A meets or exceeds all of the specifications of the Am29705.

A. THREE-STATE OUTPUTS



$$R_1 = \frac{5.0 - V_{BE} - V_{OL}}{I_{OL} + V_{OL}/1K}$$

Notes:

1. $C_L = 50\text{pF}$ includes scope probe, wiring and stray capacitances without device in test fixture.
2. S_1, S_2, S_3 are closed during function tests and all A.C. tests except output enable tests.
3. S_1 and S_3 are closed while S_2 is open to t_{pZH} test. S_1 and S_2 are closed while S_3 is open for t_{pZL} test.
4. $C_L = 5\text{pF}$ for output disable tests.

TEST OUTPUT LOADS FOR Am29705A

Pin # (DIP)	Pin Label	Test Circuit	R_1	R_2
-	$YA_0 - YA_3, YB_0 - YB_3$	A	230	1k

Notes on Testing

Incoming test procedures on this device should be carefully planned, taking into account the high complexity and power levels of the part. The following notes may be useful:

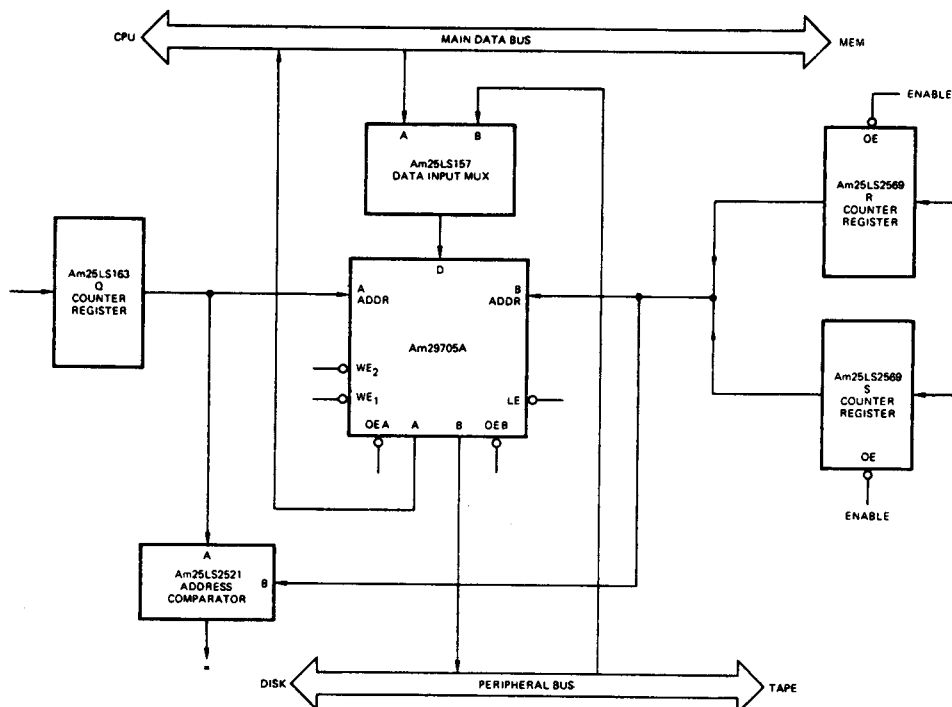
1. Insure the part is adequately decoupled at the test head. Large changes in V_{CC} current as the device switches may cause erroneous function failures due to V_{CC} changes.
2. Do not leave inputs floating during any tests, as they may start to oscillate at high frequency.
3. Do not attempt to perform threshold tests at high speed. Following an input transition, ground current may change by as much as 400mA in 5–8ns. Inductance in the ground cable may allow the ground pin at the device to rise by 100s of millivolts momentarily.
4. Use extreme care in defining input levels for AC tests. Many inputs may be changed at once, so there will be significant noise at the device pins and they may not actually reach V_{IL} or V_{IH} until the noise has settled. AMD recommends using $V_{IL} \leq 0V$ and $V_{IH} \geq 3V$ for AC tests.
5. To simplify failure analysis, programs should be designed to perform DC, Function, and AC tests as three distinct groups of tests.
6. To assist in testing, AMD offers complete documentation on our test procedures and, in most cases, can provide Fairchild Sentry programs, under license.

USING THE Am29705A AND Am29707

The Am2903 and Am29203 each contain only 16 scratch-pad registers plus the Q register. For applications which require more than 17 registers, the register set of the Am2903 and Am29203 can be easily expanded.

- Use the Am29705A with the Am2903A
- Use the Am29707 with the Am29203

For further applications information on using the Am29705A with the Am2903A, see Chapter III of *Bit Slice Microprocessor Design*, Mick and Brick, McGraw-Hill Publications.

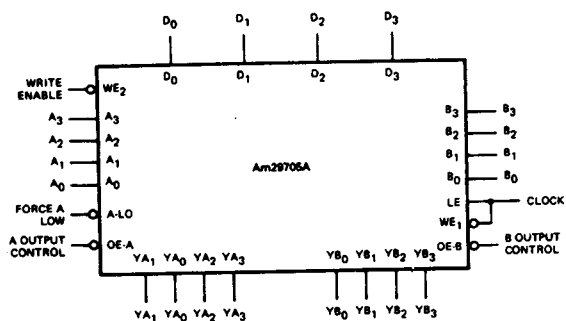


AF000270

The Am29705A as a two-way interface buffer. Data may be passed between the main data bus and the peripheral data bus under I/O control. The two-port RAM allows data to be written into buffer storage from a peripheral device, using the B address port and the S counter register, while it is being read into main memory, using the A address port and the Q counter register. This simultaneous read/write capability facilitates DMA transfers because the CPU can ignore write requests

from the peripheral device. Data output from CPU to the peripheral device is handled by sequential write and read operations. Data is written into buffer storage from the CPU, using the B address port and the R counter register. It is read onto the peripheral device using the B address port and either the R register, for single word transfers, or the S register, for block transfers.

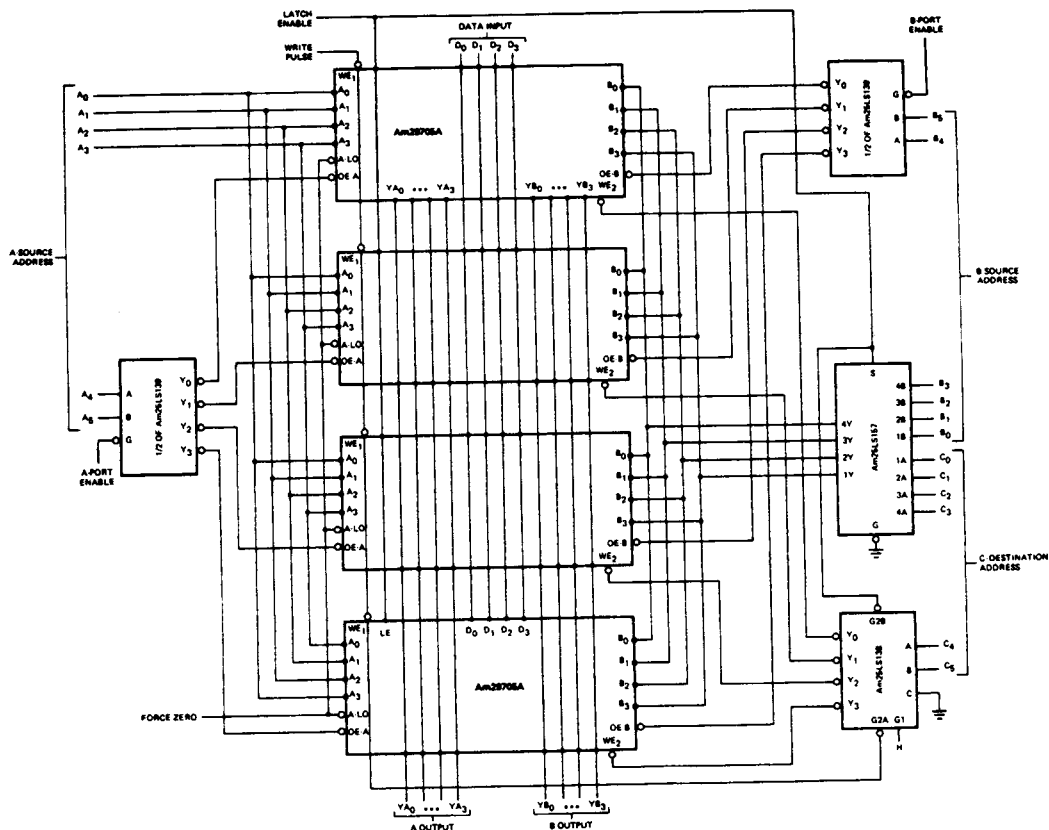
APPLICATIONS (Cont.)



LS000350

A 16-word by 4-bit two-port RAM with LE and WE₁ connected to make the device appear edge triggered. WE₁ and WE₂ are logically identical but are electrically slightly different. For

synchronous operation without possibility of race, WE₁ should be connected to LE.



AF000290

A 64-word by 4-bit three address memory. Data is read from the A address to the YA outputs and from the B address to the YB outputs while the latch enable is HIGH. When the latch enable goes LOW, the YA and YB data is held in the internal

latches, and the RAM B address is switched to the C-destination address lines. A write pulse will then deposit the input data into the location selected by the C address.



Am29203 EXPANDED MEMORY

A 48-word by 4-bit expanded memory for the Am29203 using the Am29707. The Am29751 PROM serves as a constant store.